

**ASYMMETRIC DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### Features

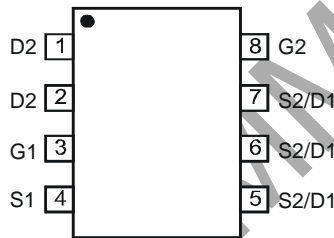
- DIOFET Utilizes a Unique Patented Process to Monolithically Integrate a MOSFET and a Schottky in a Single Die To Deliver:
  - Low  $R_{DS(on)}$ —Minimizes Conduction Loss
  - Low  $V_{SD}$ —Reduces Losses Due to Body Diode Construction
  - Low  $Q_{rr}$ —Lower  $Q_{rr}$  of Integrated Schottky Reduces Body Diode Switching Losses
  - Low Gate Capacitance ( $Q_g/Q_{gs}$ ) Ratio—Reduces Risk of Shoot-Through or Cross Conduction Currents at High Frequencies
  - Avalanche Rugged— $I_{AR}$  and  $E_{AR}$  Rated
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

### Mechanical Data

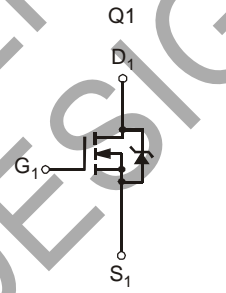
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)



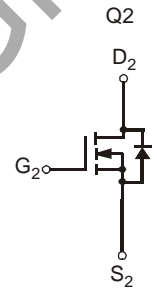
Top View



Top View  
Internal Schematic



N-Channel MOSFET +  
Integrated Schottky Diode



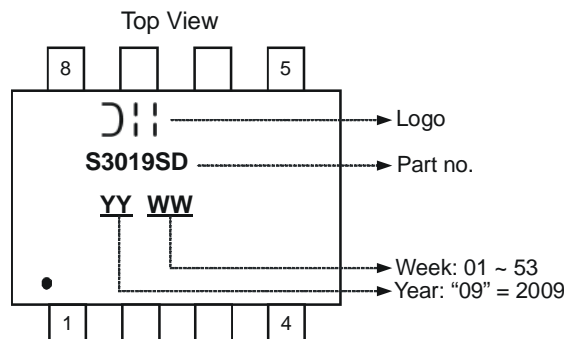
N-Channel MOSFET

### Ordering Information (Note 3)

Part Number	Case	Packaging
DMS3019SSD-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
  4. For packaging details, go to our website at <http://www.diodes.com/>.

### Marking Information



**Maximum Ratings – Q1** @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Continuous Drain Current (Note 4) $V_{GS} = 10V$	Steady State	$T_A = 25^\circ C$	$I_D$	7.0	A
		$T_A = 70^\circ C$		5.6	
Continuous Drain Current (Note 5) $V_{GS} = 10V$	Steady State	$T_A = 25^\circ C$	$I_D$	9.0	A
		$T_A = 70^\circ C$		7.0	
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$	Steady State	$T_A = 25^\circ C$	$I_D$	8.0	A
		$T_A = 70^\circ C$		6.5	
Pulsed Drain Current (Note 6)			$I_{DM}$	40	A
Avalanche Current (Notes 6 & 7)			$I_{AR}$	13	A
Repetitive Avalanche Energy (Notes 6 & 7) $L = 0.3mH$			$E_{AR}$	25.4	mJ

**Maximum Ratings – Q2** @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 4) $V_{GS} = 10V$	Steady State	$T_A = 25^\circ C$	$I_D$	5.7	A
		$T_A = 70^\circ C$		4.6	
Continuous Drain Current (Note 5) $V_{GS} = 10V$	Steady State	$T_A = 25^\circ C$	$I_D$	7.0	A
		$T_A = 70^\circ C$		5.6	
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$	Steady State	$T_A = 25^\circ C$	$I_D$	6.0	A
		$T_A = 70^\circ C$		4.7	
Pulsed Drain Current (Note 6)			$I_D$	40	A
Avalanche Current (Notes 6 & 7)			$I_{AR}$	16	A
Repetitive Avalanche Energy (Notes 6 & 7) $L = 0.1mH$			$E_{AR}$	12.8	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	$P_D$	1.19	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 4)	$R_{\theta JA}$	107	$^\circ C/W$
Power Dissipation (Note 5)	$P_D$	1.79	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 5)	$R_{\theta JA}$	70	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

- Notes:
- Device mounted on FR-4 substrate PCB, with minimum recommended pad layout. The value in any given application depends on the user's specific board design. Device contains two active die running at equal power.
  - Device mounted on 1 inch x 1 inch FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. Device contains two active die running at equal power.
  - Repetitive rating, pulse width limited by junction temperature.
  - $I_{AR}$  and  $E_{AR}$  rating are based on low frequency and duty cycles to keep  $T_J = 25^\circ C$

**Electrical Characteristics – Q1** @ T<sub>A</sub> = 25°C unless otherwise stated

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	0.1	mA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	10	15	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A
			12	18		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A
Forward Transfer Admittance	Y <sub>fs</sub>	—	5	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 9A
Diode Forward Voltage	V <sub>SD</sub>	—	0.4	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	1932	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	154	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	121	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Gate Resistance	R <sub>g</sub>	—	2.7	—		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	18.1	—	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	42.0	—		
Gate-Source Charge	Q <sub>gs</sub>	—	4.5	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	4.0	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	6.16	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>G</sub> = 3Ω, R <sub>L</sub> = 1.7Ω
Turn-On Rise Time	t <sub>r</sub>	—	7.22	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	36.76	—		
Turn-Off Fall Time	t <sub>f</sub>	—	5.38	—		

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to production testing.

NOT RECOMMENDED FOR NEW DESIGN

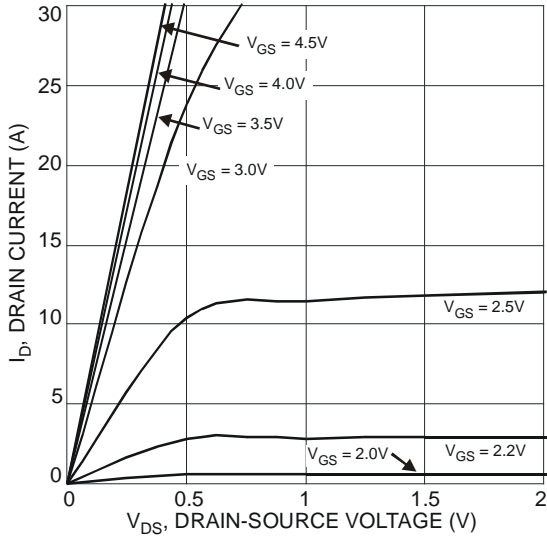


Fig. 1 Typical Output Characteristic

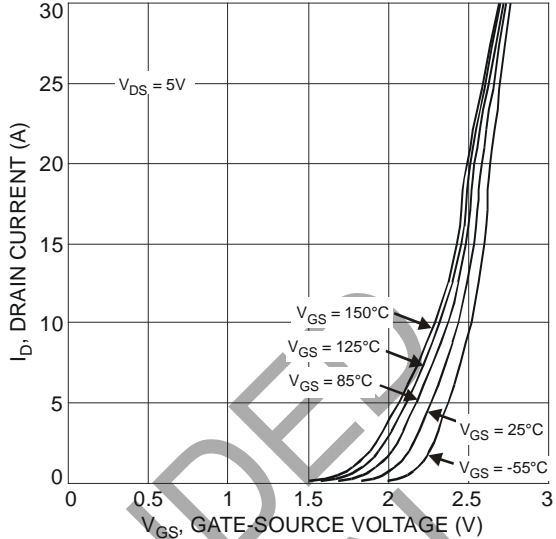


Fig. 2 Typical Transfer Characteristic

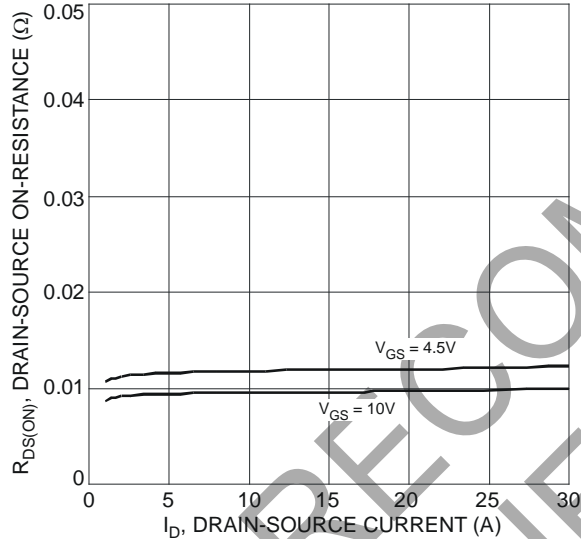


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

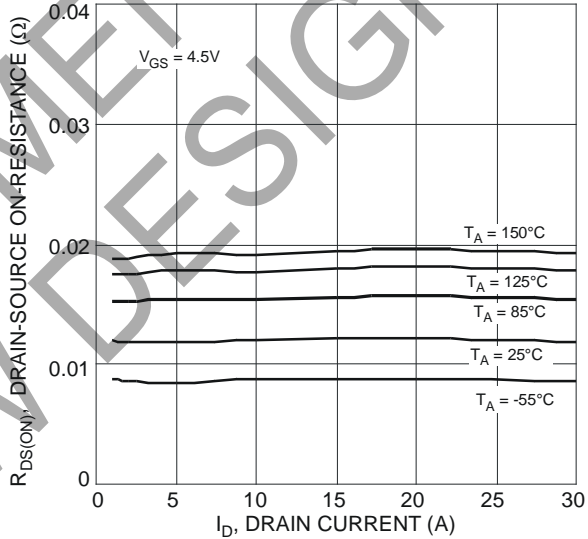


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

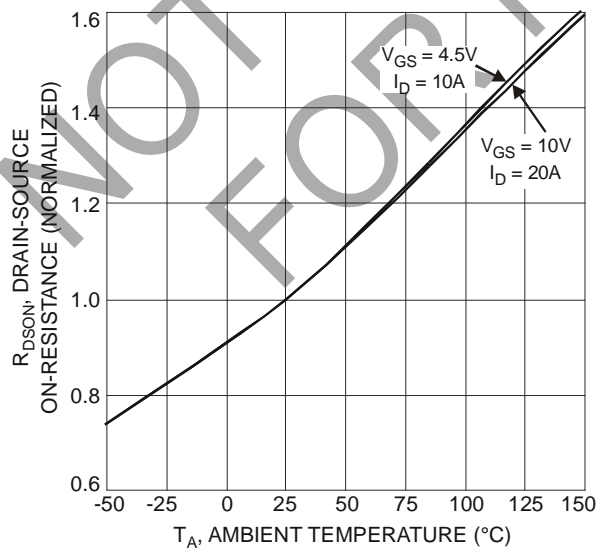


Fig. 5 On-Resistance Variation with Temperature

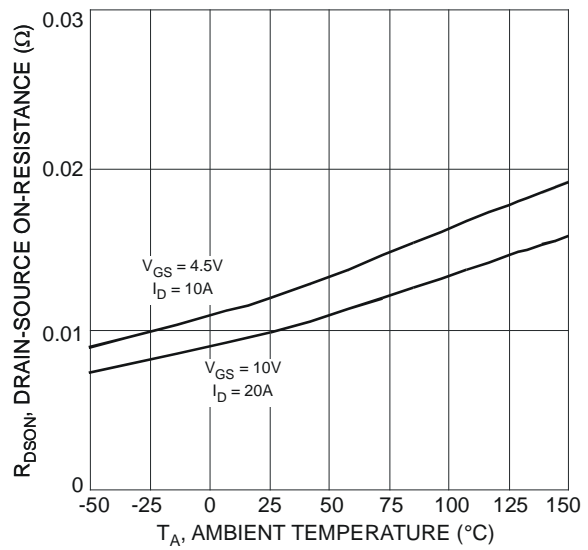


Fig. 6 On-Resistance Variation with Temperature

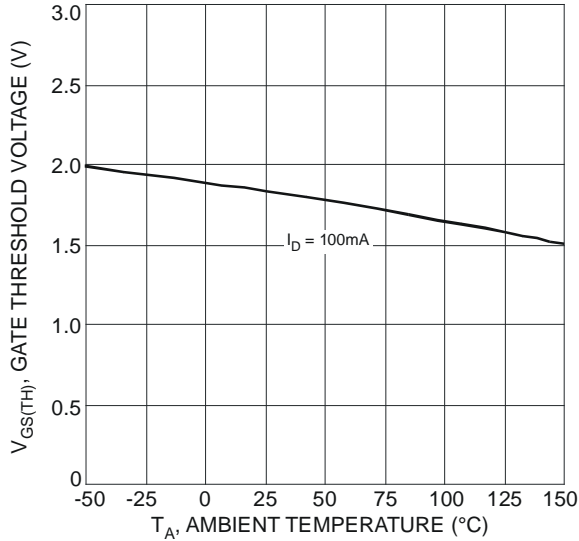


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

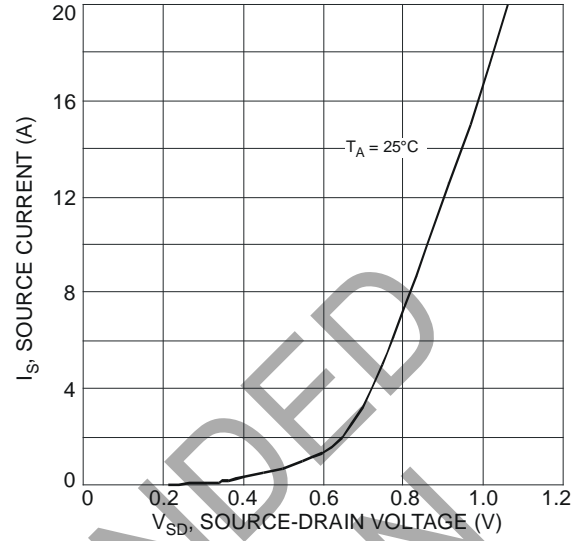


Fig. 8 Diode Forward Voltage vs. Current

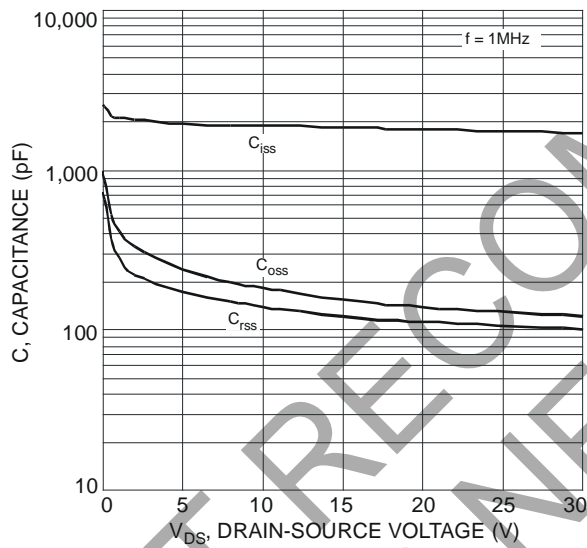


Fig. 9 Typical Total Capacitance

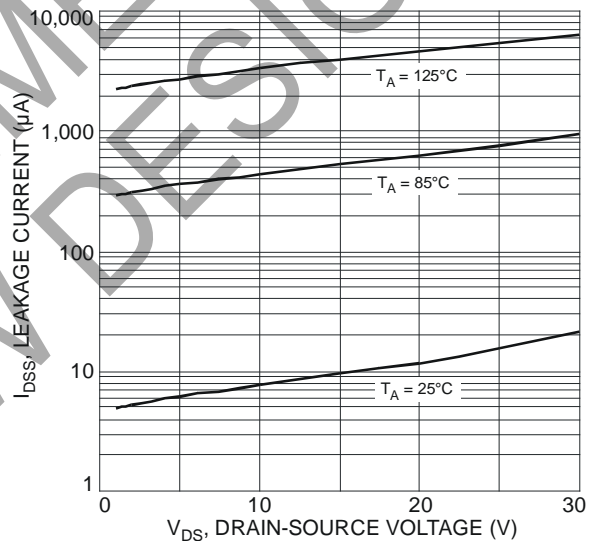


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

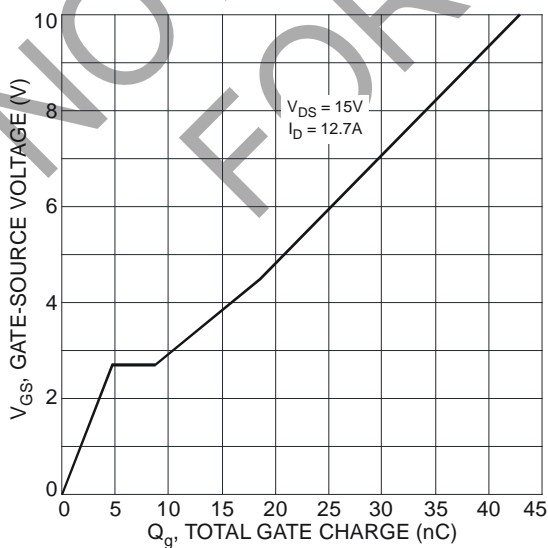
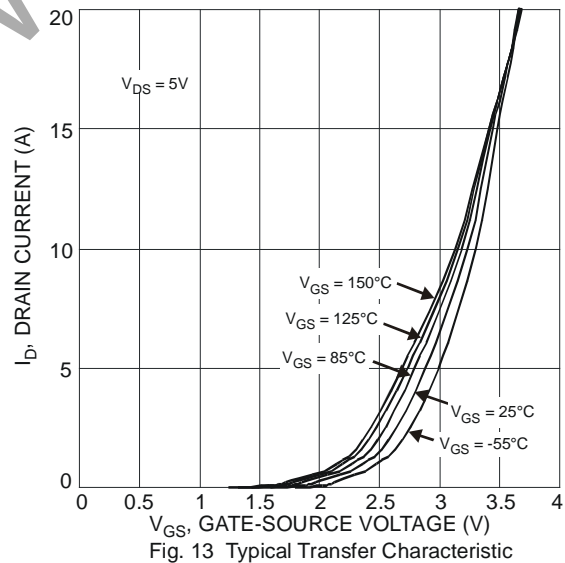
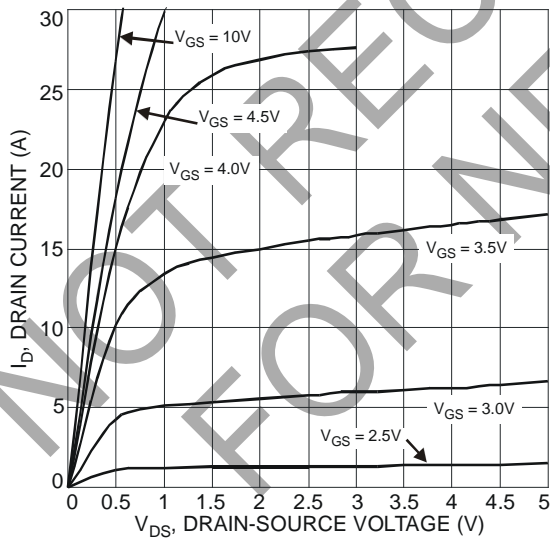


Fig. 11 Gate-Charge Characteristics

**Electrical Characteristics – Q2** @ T<sub>A</sub> = 25°C unless otherwise stated

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	15	23	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A
			25	33		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7.5A
Forward Transfer Admittance	Y <sub>fs</sub>	—	2.5	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 10A
Diode Forward Voltage	V <sub>SD</sub>	—	0.65	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	478.9	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	96.7	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	61.4	—		
Gate Resistance	R <sub>g</sub>	0.4	1.1	1.6	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.0	—	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	10.5	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.6	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	2.9	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>G</sub> = 3Ω, R <sub>L</sub> = 1.5Ω
Turn-On Rise Time	t <sub>r</sub>	—	7.9	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	14.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	3.1	—		

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to production testing.



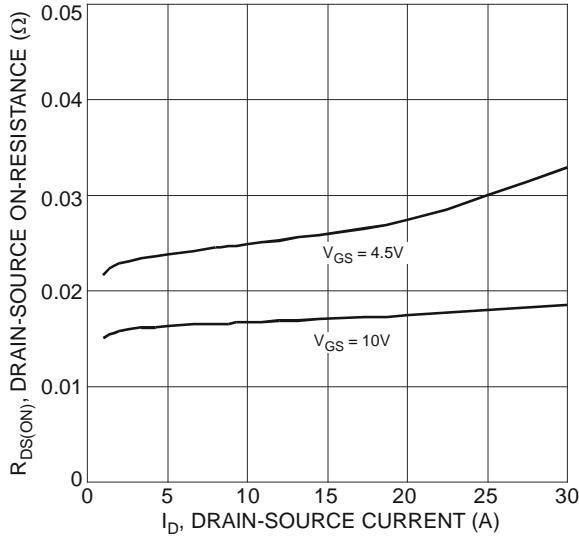


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

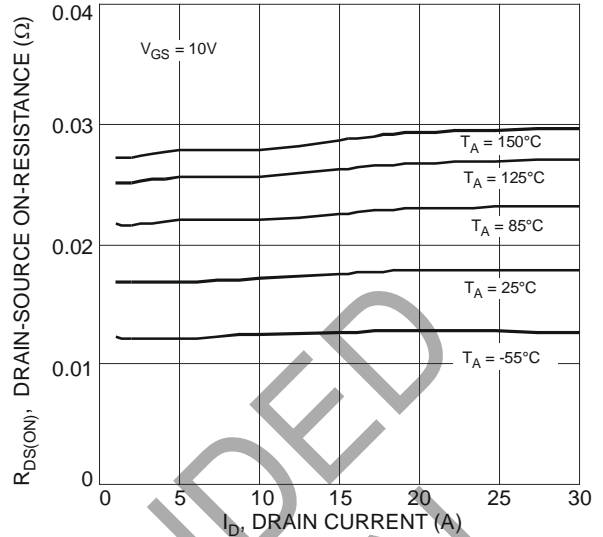


Fig. 15 Typical On-Resistance vs. Drain Current and Temperature

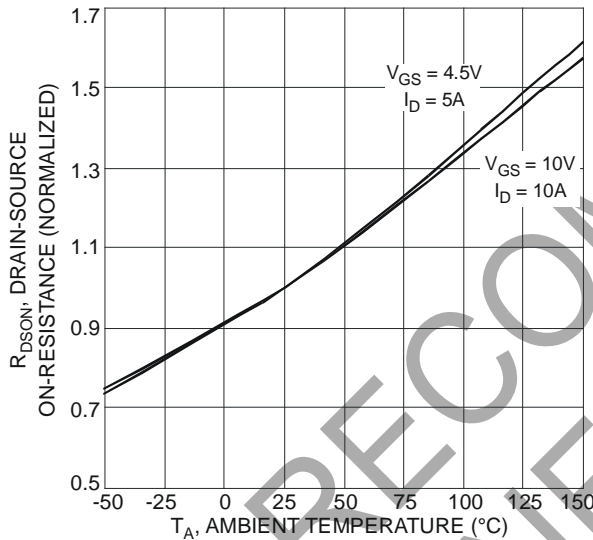


Fig. 16 On-Resistance Variation with Temperature

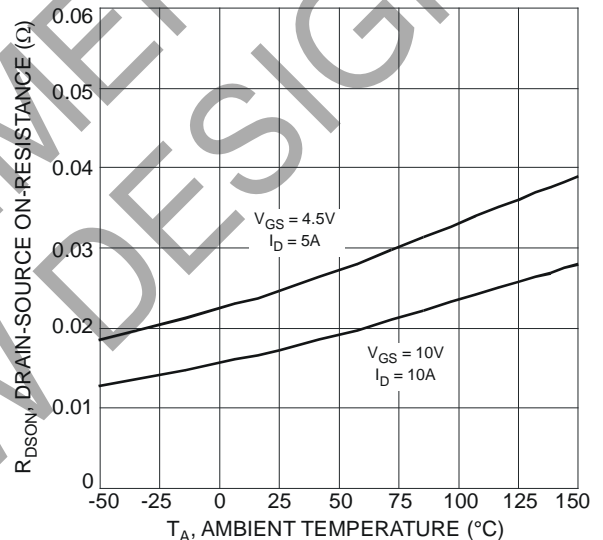


Fig. 17 On-Resistance Variation with Temperature

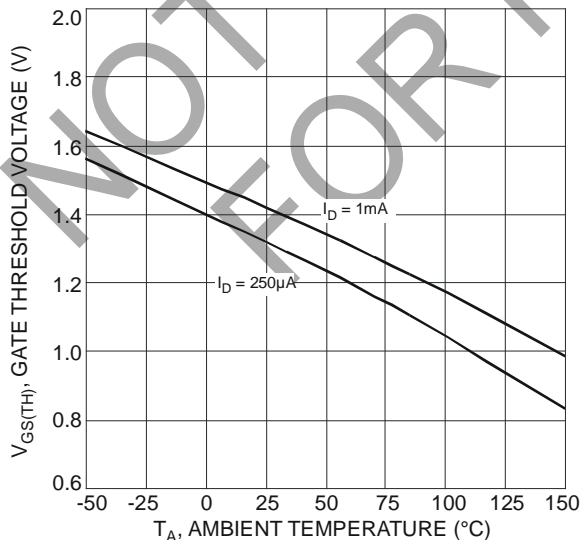


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

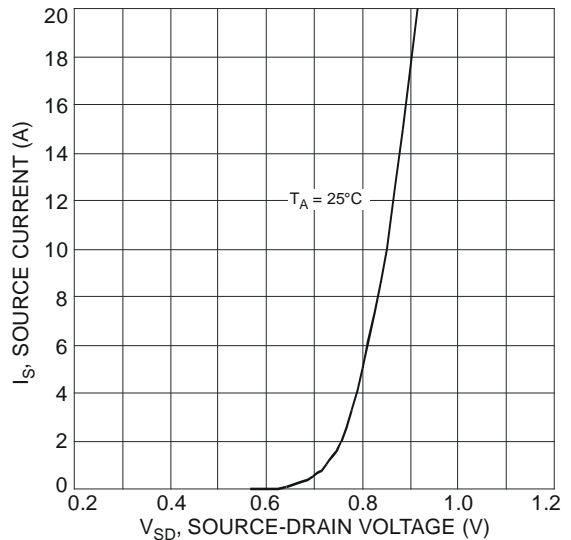


Fig. 19 Diode Forward Voltage vs. Current

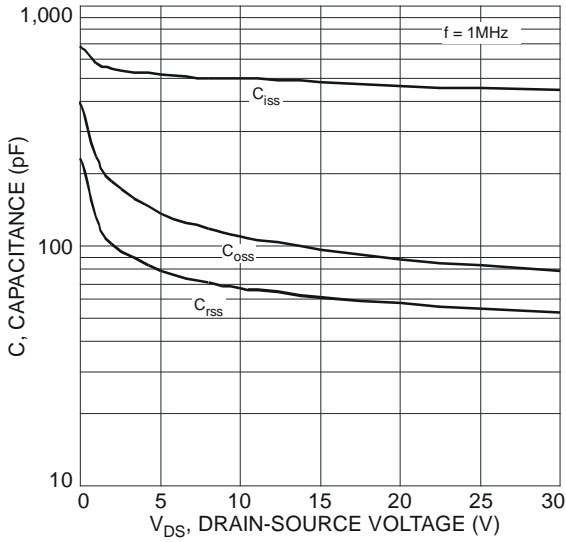


Fig. 20 Typical Total Capacitance

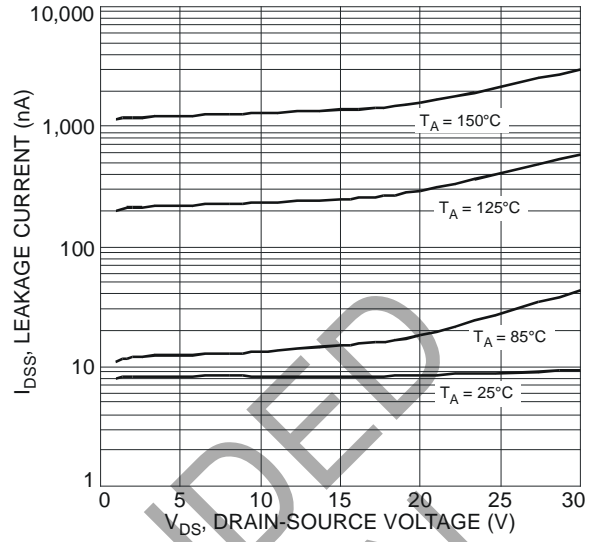


Fig. 21 Typical Leakage Current vs. Drain-Source Voltage

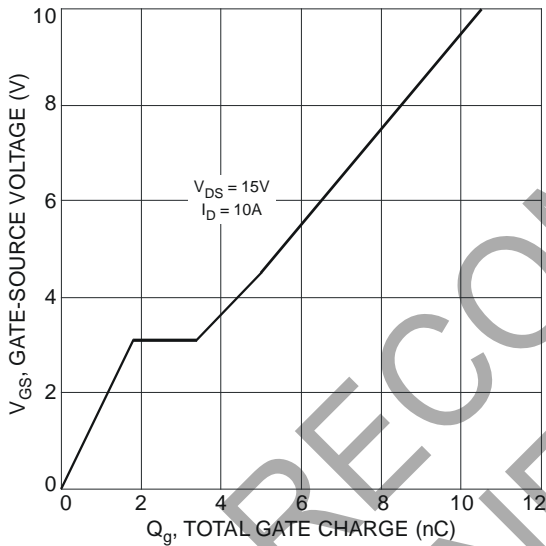


Fig. 22 Gate-Charge Characteristics

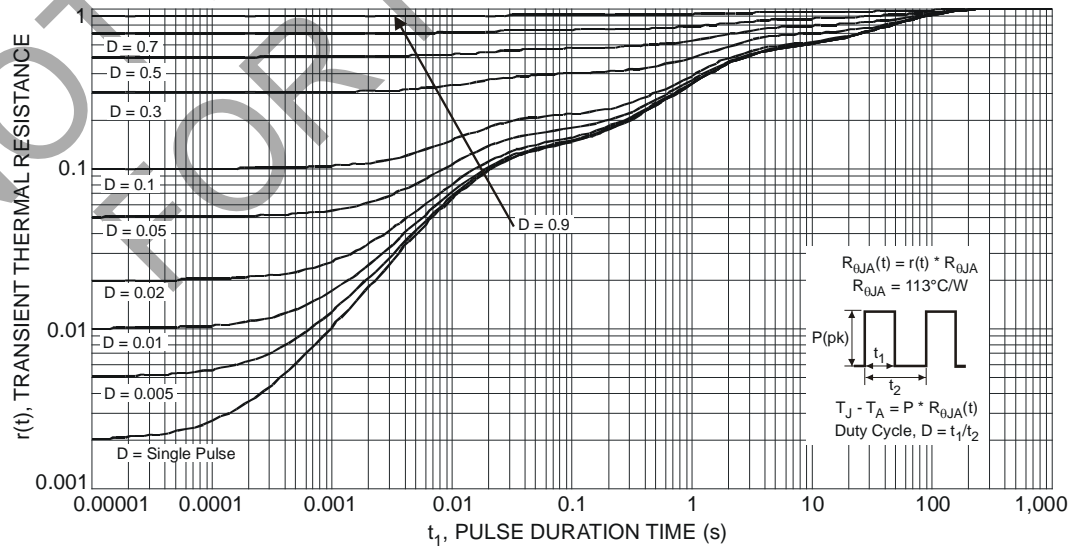


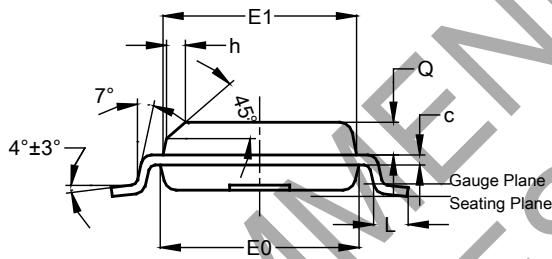
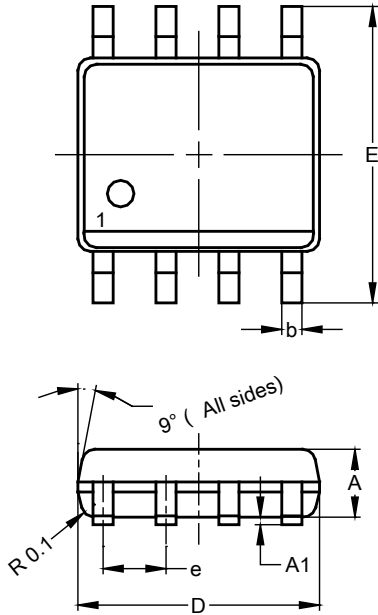
Fig. 23 Transient Thermal Response



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

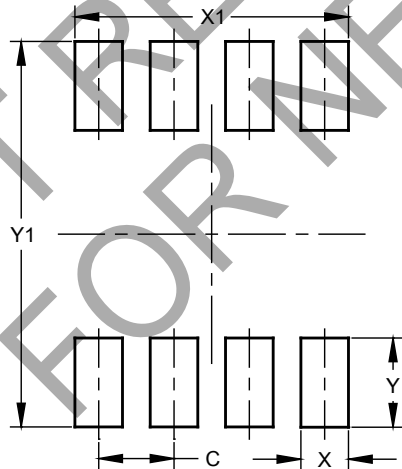


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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